

2 GHz Ultralow Distortion Differential RF/IF Amplifier

AD8352

FEATURES

-3 dB bandwidth of 2.2 GHz (A_V = 10 dB) Single resistor gain adjust: 3 dB \leq A_V \leq 25 dB Single resistor and capacitor distortion adjust Input resistance: 3 k Ω , independent of gain (A_V) Differential or single-ended input to differential output Low noise input stage: 2.7 nV/ $\sqrt{\text{Hz}}$ RTI @ A_V = 10 dB Low broadband distortion

10 MHz: -86 dBc HD2, -82 dBc HD3 70 MHz: -84 dBc HD2, -82 dBc HD3 190 MHz: -81 dBc HD2, -87 dBc HD3

OIP3 of 41 dBm @ 150 MHz

Slew rate: 8 V/ns

Fast settling and overdrive recovery of <2 ns Single-supply operation: 3 V to 5.5 V Low power dissipation: 37 mA typical @ 5 V Power-down capability: 5 mA @ 5 V

Fabricated using the high speed XFCB3 SiGe process

APPLICATIONS

Differential ADC drivers Single-ended-to-differential conversion RF/IF gain blocks SAW filter interfacing

FUNCTIONAL BLOCK DIAGRAM

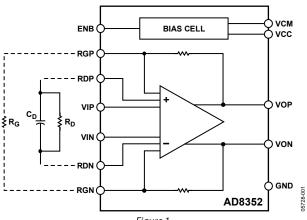


Figure 1.

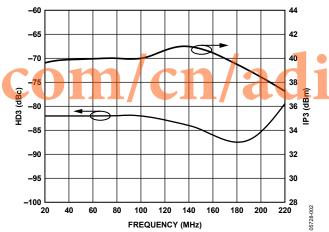


Figure 2. Third Harmonic Distortion (HD3) and IP3 vs. Frequency, Measured Differentially

GENERAL DESCRIPTION

The AD8352 is a high performance differential amplifier optimized for RF and IF applications. It achieves better than 80 dB SFDR performance at frequencies up to 200 MHz, and 65 dB beyond 500 MHz, making it an ideal driver for high speed 12-bit to 16-bit analog-to-digital converters (ADCs).

Unlike other wideband differential amplifiers, the AD8352 has buffers that isolate the gain setting resistor (R_G) from the signal inputs. As a result, the AD8352 maintains a constant 3 k Ω input resistance for gains of 3 dB to 25 dB, easing matching and input drive requirements. The AD8352 has a nominal 100 Ω differential output resistance.

The device is optimized for wideband, low distortion performance at frequencies beyond 500 MHz. These attributes, together with its wide gain adjust capability, make this device the amplifier of choice for general-purpose IF and broadband applications where low distortion, noise, and power are critical. It is ideally suited for driving not only ADCs but also mixers, pin diode attenuators, SAW filters, and multi-element discrete devices. The device is available in a compact 3 mm × 3 mm, 16-lead LFCSP and operates over a temperature range of -40°C to +85°C.

AD8352* Product Page Quick Links

Last Content Update: 08/30/2016

Comparable Parts

View a parametric search of comparable parts

Evaluation Kits

· AD8352 Evaluation Board

Documentation <a>□

Application Notes

- AN-1026: High Speed Differential ADC Driver Design Considerations
- AN-1098: Methodology for Narrow-Band Interface Design Between High Performance Differential Driver Amplifiers and ADCs

Data Sheet

 AD8352: 2 GHz Ultralow Distortion Differential RF/IF Amplifier Data Sheet

Tools and Simulations

- ADIsimPLLTM
- ADIsimRF

Reference Materials

Analog Dialogue

 Ask The Application Engineer 36, Wideband A/D Converter Front-End Design Considerations II: Amplifieror Transformer Drive for the ADC?

Product Selection Guide

· RF Source Booklet

Design Resources

- · AD8352 Material Declaration
- PCN-PDN Information
- · Quality And Reliability
- · Symbols and Footprints

Discussions <a>□

View all AD8352 EngineerZone Discussions

Sample and Buy -

Visit the product page to see pricing options

Reference Designs D

Technical Support

Submit a technical question or find your regional support number

^{*} This page was dynamically generated by Analog Devices, Inc. and inserted into this data sheet. Note: Dynamic changes to the content on this page does not constitute a change to the revision number of the product data sheet. This content may be frequently modified.

| TABL | $\mathbf{F} \wedge \mathbf{F}$ | | TENTA |
|------|--------------------------------|--------|-------|
| IVEL | _ !!_ | I-IINI | |
| IADI | г иг | 1.1114 | TENTS |

| Features | 1 |
|---|---|
| Applications | 1 |
| Functional Block Diagram | 1 |
| General Description | 1 |
| Revision History | 2 |
| Specifications | 3 |
| Noise Distortion Specifications | 4 |
| Absolute Maximum Ratings | 6 |
| ESD Caution | 6 |
| Pin Configuration and Function Descriptions | 7 |
| Typical Performance Characteristics | 8 |
| Applications Information1 | 1 |

| Gain and Distortion Adjustment (Differential Input) 11 |
|---|
| Single-Ended Input Operation |
| Narrow-Band, Third-Order Intermodulation Cancellation. 13 |
| High Performance ADC Driving14 |
| Layout and Transmission Line Effects |
| Evaluation Board |
| Evaluation Board Loading Schemes |
| Soldering Information |
| Evaluation Board Schematics |
| Outline Dimensions |
| Ordering Guide |

REVISION HISTORY

7/08—Rev. A to Rev. B

| Changes to Features Section | L |
|--|---|
| Changes to Figure 2110 |) |
| Changes to Table 9 16 | 5 |
| Added Soldering Information Section 16 | 5 |
| Changes to Figure 3817 | 7 |
| Changes to Ordering Guide | |
| | |

9/06—Rev. 0 to Rev. A

| 3/00—Rev. 0 to Rev. A | |
|--|----|
| Changes to Absolute Maximum Ratings | 6 |
| Inserted Figure 10, Figure 11, and Figure 13 | 9 |
| Inserted Figure 17, Figure 18, and Figure 21 | 10 |
| Changes to Figure 34 | 14 |
| Changes to Table 9 | 16 |
| Changes to Figure 38 | 18 |
| Changes to Ordering Guide | 19 |

1/06—Revision 0: Initial Version

C.com/cn/adi

SPECIFICATIONS

 $V_S = 5~V, R_L = 200~\Omega$ differential, $R_G = 118~\Omega$ ($A_V = 10~dB$), f = 100~MHz, T = 25°C; parameters specified differentially (in/out), unless otherwise noted. C_D and R_D are selected for differential broadband operation (see Table 5 and Table 6).

Table 1.

| Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------------------|--|------|------------|-----|--------|
| DYNAMIC PERFORMANCE | | | | | |
| –3 dB Bandwidth | $A_V = 6 \text{ dB}, V_{OUT} \le 1.0 \text{ V p-p}$ | | 2500 | | MHz |
| | $A_V = 10 \text{ dB}, V_{OUT} \le 1.0 \text{ V p-p}$ | | 2200 | | MHz |
| | $A_V = 14 \text{ dB}, V_{OUT} \le 1.0 \text{ V p-p}$ | | 1800 | | MHz |
| Bandwidth for 0.1 dB Flatness | $3 dB \le A_V \le 20 dB, V_{OUT} \le 1.0 V p-p$ | | 190 | | MHz |
| Bandwidth for 0.2 dB Flatness | $3 dB \le A_V \le 20 dB, V_{OUT} \le 1.0 V p-p$ | | 300 | | MHz |
| Gain Accuracy | Using 1% resistor for R_G , 0 dB $\leq A_V \leq$ 20 dB | | ±1 | | dB |
| Gain Supply Sensitivity | V _s ± 5% | | 0.06 | | dB/V |
| Gain Temperature Sensitivity | -40°C to +85°C | | 4 | | mdB/°0 |
| Slew Rate | $R_L = 1 \text{ k}\Omega$, $V_{OUT} = 2 \text{ V step}$ | | 9 | | V/ns |
| | $R_L = 200 \Omega$, $V_{OUT} = 2 V$ step | | 8 | | V/ns |
| Settling Time | 2 V step to 1% | | <2 | | ns |
| Overdrive Recovery Time | $V_{IN} = 4 \text{ V to } 0 \text{ V step, } V_{OUT} \leq \pm 10 \text{ mV}$ | | <3 | | ns |
| Reverse Isolation (S12) | | | -80 | | dB |
| INPUT/OUTPUT CHARACTERISTICS | | | | | |
| Common-Mode Nominal | | | VCC/2 | | V |
| Voltage Adjustment Range | | | 1.2 to 3.8 | | V |
| Maximum Output Voltage Swing | 1 dB compressed | | 6 | | V p-p |
| Output Common-Mode Offset | Referenced to VCC/2 | -100 | | +20 | mV |
| Output Common-Mode Drift | -40°C to +85°C | | 0.25 | 2 | mV/°C |
| Output Differential Offset Voltage | | -20 | /11/ | +20 | mV |
| Common-Mode Rejection Ratio (CMRR) | | | 57 | | dB |
| Output Differential Offset Drift | −40°C to +85°C | | 0.15 | | mV/°C |
| Input Bias Current | | | ±5 | | μΑ |
| Input Resistance | | | 3 | | kΩ |
| Input Capacitance (Single Ended) | | | 0.9 | | рF |
| Output Resistance | | | 100 | | Ω |
| Output Capacitance | | | 3 | | рF |
| POWER INTERFACE | | | | | |
| Supply Voltage | | 3 | 5 | 5.5 | V |
| ENB Threshold | | | 1.5 | | V |
| ENB Input Bias Current | ENB at 3 V | | 75 | | nA |
| · | ENB at 0.6 V | | -125 | | μΑ |
| Quiescent Current | ENB at 3 V | 35 | 37 | 39 | mA |
| | ENB at 0.6 V | | 5.3 | | mA |

NOISE DISTORTION SPECIFICATIONS

 $V_S = 5 \text{ V}$, $R_L = 200 \Omega$ differential, $R_G = 118 \Omega$ ($A_V = 10 \text{ dB}$), $V_{OUT} = 2 \text{ V}$ p-p composite, $T = 25^{\circ}\text{C}$; parameters specified differentially, unless otherwise noted. C_D and R_D are selected for differential broadband operation (see Table 5 and Table 6). See the Applications Information section for single-ended-to-differential performance characteristics.

Table 2.

| Parameter | Conditions | Min Typ Max | Unit |
|--|---|-----------------|---------------|
| 10 MHz | | | |
| Second/Third Harmonic Distortion ¹ | $R_L = 1 \text{ k}\Omega$, $V_{OUT} = 2 \text{ V p-p}$ | -88/-95 | dBc |
| | $R_L = 200 \Omega$, $V_{OUT} = 2 V p-p$ | -86/-82 | dBc |
| Output Third-Order Intercept | $R_L = 200 \Omega$, $f_1 = 9.5 MHz$, $f_2 = 10.5 MHz$ | 38 | dBm |
| Third-Order IMD | $R_L = 1 \text{ k}\Omega$, $f_1 = 9.5 \text{ MHz}$, $f_2 = 10.5 \text{ MHz}$, $V_{OUT} = 2 \text{ V p-p composite}$ | -86 | dBc |
| | $R_L = 200 \Omega$, $f_1 = 9.5 MHz$, $f_2 = 10.5 MHz$, $V_{OUT} = 2 V p-p composite$ | -81 | dBc |
| Noise Spectral Density (RTI) | | 2.7 | nV/√Hz |
| 1 dB Compression Point (RTO) | | 15.7 | dBm |
| 70 MHz | | | |
| Second/Third Harmonic Distortion | $R_L = 1 \text{ k}\Omega$, $R_G = 178 \Omega$, $V_{OUT} = 2 \text{ V p-p}$ | -83/-84 | dBc |
| | $R_L = 200 \Omega$, $R_G = 115 \Omega$, $V_{OUT} = 2 V p-p$ | -84/-82 | dBc |
| Output Third-Order Intercept | $R_L = 200 \Omega$, $f_1 = 69.5 MHz$, $f_2 = 70.5 MHz$ | 40 | dBm |
| Third-Order IMD | $R_L = 1 \text{ k}\Omega$, $f_1 = 69.5 \text{ MHz}$, $f_2 = 70.5 \text{ MHz}$, $V_{OUT} = 2 \text{ V p-p composite}$ | -91 | dBc |
| | $R_L = 200 \Omega$, $f_1 = 69.5 MHz$, $f_2 = 70.5 MHz$, | -83 | dBc |
| | $V_{OUT} = 2 V p-p composite$ | | . - |
| Noise Spectral Density (RTI) 1 dB Compression Point (RTO) | | 2.7 15.7 | nV/√Hz dBm |
| 1 <mark>00 MHz</mark> | | | |
| Second/Third Harmonic Distortion | $R_L = 1 \text{ k}\Omega$, $V_{OUT} = 2 \text{ V p-p}$ | -83/-83 | dBc |
| | $R_L = 200 \Omega, V_{OUT} = 2 V p-p$ | -84/-82 | dBc |
| Output Third-Order Intercept | $R_L = 200 \Omega$, $f_1 = 99.5 \text{ MHz}$, $f_2 = 100.5 \text{ MHz}$ | 40 | dBm |
| Third-Order IMD | $R_L = 1 \text{ k}\Omega$, $f_1 = 99.5 \text{ MHz}$, $f_2 = 100.5 \text{ MHz}$, $V_{OUT} = 2 \text{ V p-p composite}$ | - 91 | dBc |
| | $R_L = 200 \ \Omega, \ f_1 = 99.5 \ MHz, \ f_2 = 100.5 \ MHz, \ V_{OUT} = 2 \ V \ p-p \ composite$ | -84 | dBc |
| Noise Spectral Density (RTI) | | 2.7 | nV/√Hz |
| 1 dB Compression Point (RTO) | | 15.6 | dBm |
| 140 MHz | | | |
| Second/Third Harmonic Distortion | $R_L = 1 \text{ k}\Omega$, $V_{OUT} = 2 \text{ V p-p}$ | -83/-82 | dBc |
| | $R_L = 200 \Omega, V_{OUT} = 2 V p-p$ | -82/-84 | dBc |
| Output Third-Order Intercept | $R_L = 200 \Omega$, $f_1 = 139.5 MHz$, $f_2 = 140.5 MHz$ | 41 | dBm |
| Third-Order IMD | $R_L = 1 \text{ k}\Omega$, $f_1 = 139.5 \text{ MHz}$, $f_2 = 140.5 \text{ MHz}$, $V_{OUT} = 2 \text{ V p-p composite}$ | -89 | dBc |
| | $R_L = 200 \Omega$, $f_1 = 139.5 \text{ MHz}$, $f_2 = 140.5 \text{ MHz}$, $V_{OUT} = 2 \text{ V p-p composite}$ | -85 | dBc |
| Noise Spectral Density (RTI) | | 2.7 | nV/√Hz |
| 1 dB Compression Point (RTO) | | 15.5 | dBm |

| Parameter | Conditions | Min Typ Max | Unit |
|---|--|-----------------|------------|
| 190 MHz | | | |
| Second/Third Harmonic Distortion | $R_L = 1 \text{ k}\Omega$, $V_{OUT} = 2 \text{ V p-p}$ | -82/-85 | dBc |
| | $R_L = 200 \Omega, V_{OUT} = 2 V p-p$ | -81/-87 | dBc |
| Output Third-Order Intercept | $R_L = 200 \Omega$, $f_1 = 180.5 MHz$, $f_2 = 190.5 MHz$ | 39 | dBm |
| Third-Order IMD | $R_L=1$ k Ω , $f_1=180.5$ MHz, $f_2=190.5$ MHz, $V_{OUT}=2$ V p-p composite | -83 | dBc |
| | $R_L = 200 \ \Omega, f_1 = 180.5 \ MHz, f_2 = 190.5 \ MHz,$ $V_{OUT} = 2 \ V \ p-p \ composite$ | -81 | dBc |
| Noise Spectral Density (RTI) | | 2.7 | nV/√Hz |
| 1 dB Compression Point (RTO) | | 15.4 | dBm |
| 240 MHz | | | |
| Second/Third Harmonic Distortion | $R_L = 1 \text{ k}\Omega$, $V_{OUT} = 2 \text{ V p-p}$ | -82/-76 | dBc |
| | $R_L = 200 \Omega, V_{OUT} = 2 V p-p$ | -80/-73 | dBc |
| Output Third-Order Intercept | $R_L = 200 \Omega$, $f_1 = 239.5 \text{ MHz}$, $f_2 = 240.5 \text{ MHz}$ | 36 | dBm |
| Third-Order IMD | $R_L = 1$ k Ω , $f_1 = 239.5$ MHz, $f_2 = 240.5$ MHz, $V_{OUT} = 2$ V p-p composite | -85 | dBc |
| | $R_L = 200 \ \Omega, f_1 = 239.5 \ MHz, f_2 = 240.5 \ MHz, V_{OUT} = 2 \ V \ p-p \ composite$ | –77 | dBc |
| Noise Spectral Density (RTI) | | 2.7 | nV/√Hz |
| 1 dB Compression Point (RTO) | | 15.3 | dBm |
| 380 MHz | | | |
| Second/Third Harmonic Distortion ² | $R_L = 1 \text{ k}\Omega$, $V_{OUT} = 2 \text{ V p-p}$ | -72/-68 | dBc |
| | $R_L = 200 \Omega, V_{OUT} = 2 V p-p$ | -74/-69 | dBc |
| Output Third-Order Intercept | $R_L = 200 \Omega$, $f_1 = 379.5 MHz$, $f_2 = 380.5 MHz$ | 33 | dBm |
| Third-Order IMD | $R_L = 1 \text{ k}\Omega$, $f_1 = 379.5 \text{ MHz}$, $f_2 = 380.5 \text{ MHz}$, $V_{OUT} = 2 \text{ V p-p composite}$ $R_L = 200 \Omega$, $f_1 = 379.5 \text{ MHz}$, $f_2 = 380.5 \text{ MHz}$, $V_{OUT} = 2 \text{ V p-p composite}$ | C_{70}^{-74} | dBc dBc |
| Noise Spectral Density (RTI) | | 2.7 | nV/√Hz |
| 1 dB Compression Point (RTO) | | 14.6 | dBm |
| 500 MHz | | | |
| Second/Third Harmonic Distortion ² | $R_L = 200 \Omega, V_{OUT} = 2 V p-p$ | -71/-64 | dBc |
| Output Third-Order Intercept | $R_L = 200 \Omega$, $f_1 = 499.5 \text{ MHz}$, $f_2 = 500.5 \text{ MHz}$ | 28 | dBm |
| Third-Order IMD | $R_L = 200 \ \Omega, f_1 = 499.5 \ MHz, f_2 = 500.5 \ MHz,$ $V_{OUT} = 2 \ V \ p-p \ composite$ | - 61 | dBc |
| Noise Spectral Density (RTI) | | 2.7 | nV/√Hz |
| 1 dB Compression Point (RTO) | | 13.9 | dBm |

¹ When using the evaluation board at frequencies below 50 MHz, replace the Output Balun T1 with a transformer, such as Mini-Circuits® ADT1-1WT to obtain the low frequency balance required for differential HD2 cancellation.
² C_D and R_D can be optimized for broadband operation below 180 MHz. For operation above 300 MHz, C_D and R_D components are not required.

ABSOLUTE MAXIMUM RATINGS

Table 3.

| Parameter | Rating |
|-------------------------------------|-----------------|
| Supply Voltage, VCC | 5.5 V |
| VIP, VIN | VCC + 0.5 V |
| Internal Power Dissipation | 210 mW |
| Θ_{JA} | 91.4°C/W |
| Maximum Junction Temperature | 125°C |
| Operating Temperature Range | −40°C to +85°C |
| Storage Temperature Range | −65°C to +150°C |
| Lead Temperature (Soldering 60 sec) | 300°C |

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

www.BDTIC.com/cn/adi

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

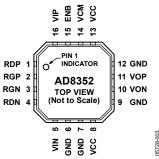


Figure 3. Pin Configuration

Table 4. Pin Function Descriptions

| Pin No. | Mnemonic | Description |
|-------------|------------|---|
| 1 | RDP | Positive Distortion Adjust. |
| 2 | RGP | Positive Gain Adjust. |
| 3 | RGN | Negative Gain Adjust. |
| 4 | RDN | Negative Distortion Adjust. |
| 5 | VIN | Balanced Differential Input. This pin is biased to VCM, typically ac-coupled. |
| 6, 7, 9, 12 | GND | Ground. Connect this pin to low impedance GND. |
| 8, 13 | VCC | Positive Supply. |
| 10 | VON VOP | Balanced Differential Output. This pin is biased to VCM, typically ac-coupled. Balanced Differential Output. This pin is biased to VCM, typically ac-coupled. |
| 14 | VCM | Common-Mode Voltage. A voltage applied to this pin sets the common-mode voltage of the input and output. Typically decoupled to ground with a 0.1 μ F capacitor. With no reference applied, input and output common mode floats to midsupply (VCC/2). |
| 15 | ENB | Enable. Apply positive voltage (1.3 V < ENB < VCC) to activate device. |
| 16 | VIP | Balanced Differential Input. This pin is biased to VCM, typically ac-coupled. |

TYPICAL PERFORMANCE CHARACTERISTICS

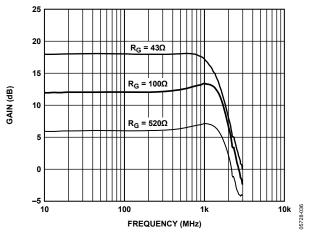


Figure 4. Gain vs. Frequency for a 200 Ω Differential Load with Baluns, $A_V = 18$ dB, 12 dB, and 6 dB

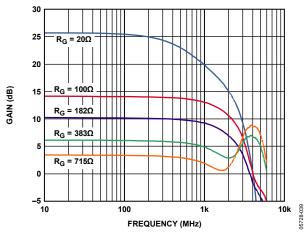


Figure 7. Gain vs. Frequency for a 1 k Ω Differential Load Without Baluns, R_D/C_D Open, $A_V = 25$ dB, 14 dB, 10 dB, 6 dB, and 3 dB

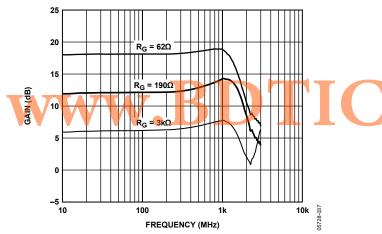


Figure 5. Gain vs. Frequency for a 1 k Ω Differential Load with Baluns, $A_V=$ 18 dB, 12 dB, and 6 dB

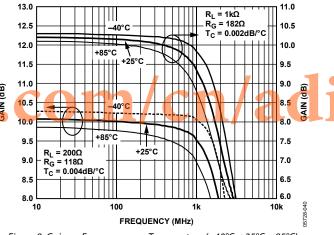


Figure 8. Gain vs. Frequency over Temperature ($-40^{\circ}C$, $+25^{\circ}C$) Without Baluns, $A_V=10$ dB, $R_L=200$ Ω and 1 k Ω

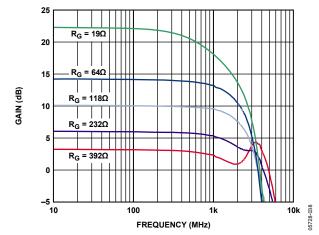


Figure 6. Gain vs. Frequency for a 200 Ω Differential Load Without Baluns, R_D/C_D Open, $A_V=22$ dB, 14 dB, 10 dB, 6 dB, and 3 dB

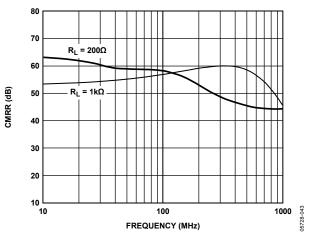


Figure 9. CMRR vs. Frequency, $R_L = 200 \Omega$ and 1 $k\Omega$, Differential Source Resistance

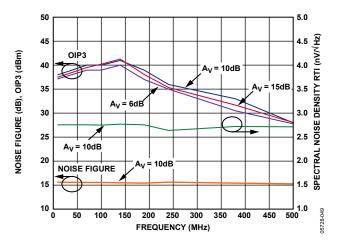


Figure 10. Noise Figure, OIP3, and Spectral Noise Density vs. Frequency, 2 V p-p Composite, $R_L = 200 \Omega$

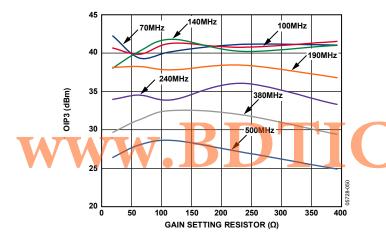


Figure 11. Output IP3 (OIP3) vs. R_G for Multiple Frequencies, R_L = 200 Ω

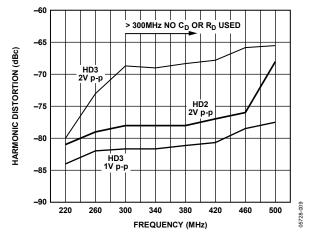


Figure 12. Third-Order Harmonic Distortion (HD3) vs. Frequency, $A_V=10~dB,\,R_L=200~\Omega$

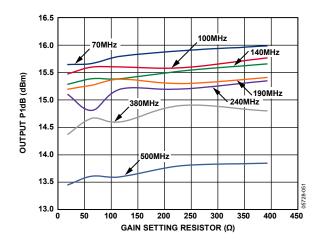


Figure 13. Output 1 dB Compression Point (P1dB) vs. R_G for Multiple Frequencies, $R_L = 200 \Omega$

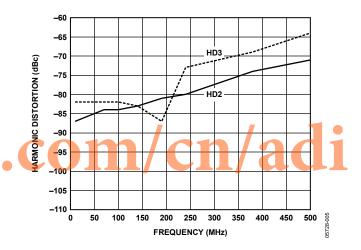


Figure 14. Harmonic Distortion vs. Frequency for 2 V p-p into $R_L = 1 \, k\Omega$, $A_V = 10 \, dB$, 5 V Supply, $R_G = 180 \, \Omega$, $R_D = 6.8 \, k\Omega$, $C_D = 0.1 \, pF$

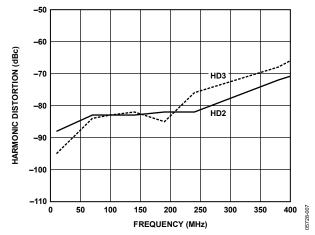


Figure 15. Harmonic Distortion vs. Frequency for 2 V p-p into $R_L = 200 \Omega$, $A_V = 10$ dB, $R_G = 115 \Omega$, $R_D = 4.3$ k Ω , $C_D = 0.2$ pF

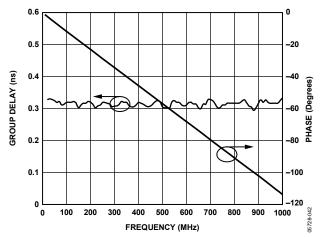


Figure 16. Group Delay and Phase vs. Frequency, $A_V = 10$ dB, $R_L = 200 \Omega$

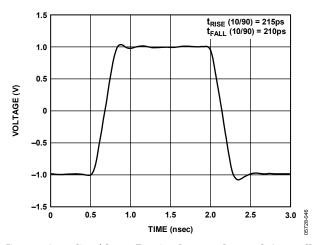


Figure 19. Large Signal Output Transient Response, $R_L = 200 \Omega$, $A_V = 10 dB$.

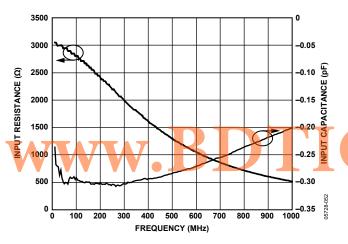


Figure 17. S11 Equivalent RC Parallel Network, $R_G = 115 \Omega$

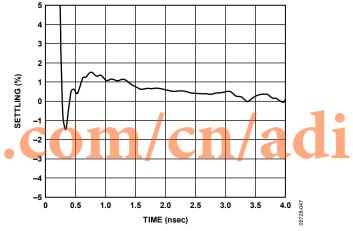


Figure 20. 1% Settling Time for a 2 V p-p Step Response, $A_V = 10$ dB, $R_L = 200 \Omega$

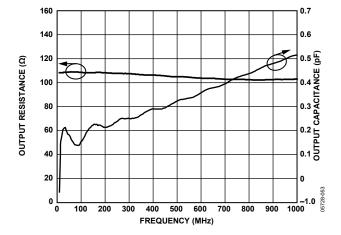


Figure 18. S22 Equivalent RC Parallel Network, $R_G = 115 \Omega$

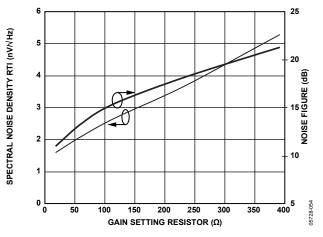


Figure 21. Spectral Noise Density RTI and Noise Figure vs. R_G , $R_L = 200 \Omega$

APPLICATIONS INFORMATION GAIN AND DISTORTION ADJUSTMENT (DIFFERENTIAL INPUT)

Table 5 and Table 6 show the required value of R_G for the gains specified at 200 Ω and 1 $k\Omega$ loads. Figure 22 and Figure 24 plot gain vs. R_G up to 18 dB for both load conditions. For other output loads (R_L) , use Equation 1 to compute gain vs. R_G .

$$A_{VDifferential} = \left(\frac{R_G + 500}{(R_G + 5)(R_L + 53) + 430}\right) R_L \tag{1}$$

where

 R_L is the single-ended load.

 R_G is the gain setting resistor.

The third-order harmonic distortion can be reduced by using external components $R_{\rm D}$ and $C_{\rm D}$. Table 5 and Table 6 show the required values for $R_{\rm D}$ and $C_{\rm D}$ for the specified gains to achieve (single tone) third-order distortion reduction at 180 MHz. Figure 23 and Figure 25 show any gain (up to 18 dB) vs. $C_{\rm D}$ for 200 Ω and 1 k Ω loads, respectively. When these values are selected, they result in minimum single tone, third-order distortion at 180 MHz. This frequency point provides the best overall broadband distortion for the specified frequencies below and above this value. For applications above $\sim\!300$ MHz, $C_{\rm D}$ and $R_{\rm D}$ are not required. See the Specifications section and the third-order harmonic plots for more details (see Figure 12, Figure 14, and Figure 15).

 C_D can be further optimized for narrow-band tuning requirements below 180 MHz that result in relatively lower third-order (inband) intermodulation distortion terms. See the Narrow-Band, Third-Order Intermodulation Cancellation section for more information. Though not shown, single tone, third-order optimization can also be improved for narrow-band frequency applications below 180 MHz with the proper selection of C_D , and 3 dB to 6 dB of relative third-order improvement can be realized at frequencies below approximately 140 MHz.

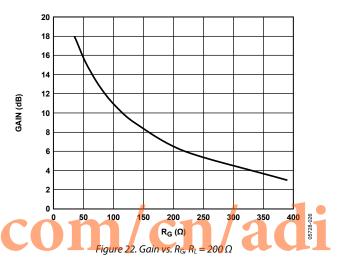
Using the information listed in Table 5 and Table 6, an extrapolated value for R_D can be determined for loads between 200 Ω and 1 k Ω . For loads above 1 k Ω , use the 1 k Ω R_D values listed in Table 6.

Table 5. Broadband Selection of RG, CD, and RD, 200 Ω Load

| A _V (dB) | R _G (Ω) | C _D (pF) | R _D (kΩ) |
|---------------------|--------------------|---------------------|---------------------|
| 3 | 390 | Open | 6.8 |
| 6 | 220 | Open | 4.3 |
| 9 | 140 | 0.1 | 4.3 |
| 10 | 115 | 0.2 | 4.3 |
| 12 | 86 | 0.3 | 4.3 |
| 15 | 56 | 0.6 | 4.3 |
| 18 | 35 | 1 | 4.3 |

Table 6. Broadband Selection of R_G, C_D, and R_D, 1 kΩ Load

| A _V (dB) | R _G (Ω) | C _D (pF) | $R_D(k\Omega)$ |
|---------------------|--------------------|---------------------|----------------|
| 3 | 750 | Open | 6.8 |
| 6 | 360 | Open | 6.8 |
| 9 | 210 | Open | 6.8 |
| 10 | 180 | 0.05 | 6.8 |
| 12 | 130 | 0.1 | 6.8 |
| 15 | 82 | 0.3 | 6.8 |
| 18 | 54 | 0.5 | 6.8 |



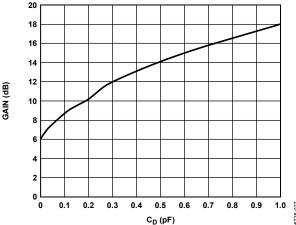
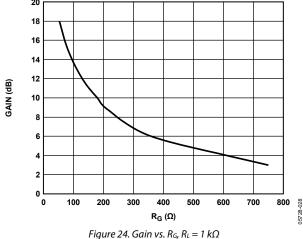


Figure 23. Gain vs. C_D , $R_L = 200 \Omega$



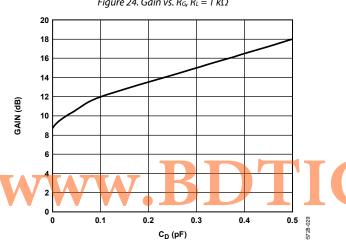


Figure 25. Gain vs. C_D , $R_L = 1 k\Omega$

SINGLE-ENDED INPUT OPERATION

The AD8352 can be configured as a single-ended-to-differential amplifier, as shown in Figure 26. To balance the outputs when driving the VIP input, an external resistor (R_N) of 200 Ω is added between VIP and RGN. See Equation 2 to determine the single-ended input gain ($A_{V \; Single-Ended}$) for a given R_G or R_L .

$$A_{VSingle-Ended} = \left(\frac{R_G + 500}{(R_G + 5)(R_L + 53) + 430}\right) R_L + \frac{R_L}{R_L + 30}$$
(2)

where

 R_L is the single-ended load.

 R_G is the gain setting resistor.

Figure 27 plots gain vs. R_G for 200 Ω and 1 $k\Omega$ loads. Table 7 and Table 8 show the values of C_D and R_D required (for 180 MHz broadband, third-order, single tone optimization) for 200 Ω and 1 $k\Omega$ loads, respectively. This single-ended configuration provides -3 dB bandwidths similar to input differential drive. Figure 28 through Figure 31 show distortion levels at a gain of 12 dB for both 200 Ω and 1 $k\Omega$ loads. Gains from 3 dB to 18 dB, using optimized C_D and R_D values, obtain similar distortion levels.

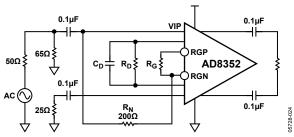


Figure 26. Single-Ended Schematic

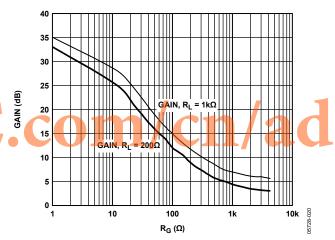


Figure 27. Gain vs. R_G

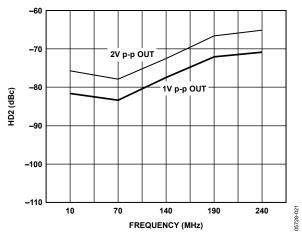


Figure 28. Single-Ended, Second-Order Harmonic Distortion (HD2) vs. Frequency, $200\,\Omega\,\text{Load}$

This broadband optimization was also performed at 180 MHz. As with differential input drive, the resulting distortion levels at lower frequencies are based on the C_D and R_D specified in Table 7 and Table 8. As with differential input drive, relative third-order reduction improvement at frequencies below 140 MHz is realized with proper selection of C_D and R_D .

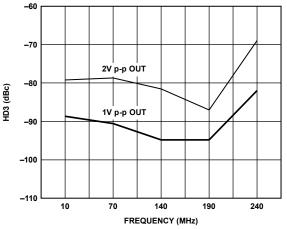


Figure 29. Single-Ended, Third-Order Harmonic Distortion (HD3) vs. Frequency, 200 Ω Load

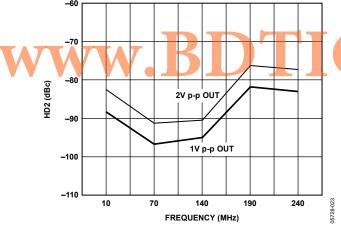


Figure 30. Single-Ended, Second-Order Harmonic Distortion (HD2) vs. Frequency, $1 \text{ k}\Omega$ Load

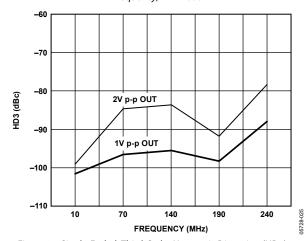


Figure 31. Single-Ended, Third-Order Harmonic Distortion (HD3) vs. Frequency, 1 $k\Omega$ Load

Table 7. Distortion Cancellation Selection Components (R_D and C_D) for Required Gain, 200 Ω Load

| A _V (dB) | R _G (Ω) | $C_D(pF)$ $R_D(k\Omega)$ | |
|---------------------|--------------------|--------------------------|-----|
| 3 | 4.3 k | Open | 4.3 |
| 6 | 540 | Open | 4.3 |
| 9 | 220 | 0.1 | 4.3 |
| 12 | 120 | 0.3 | 4.3 |
| 15 | 68 | 0.6 | 4.3 |
| 18 | 43 | 0.9 | 4.3 |

Table 8. Distortion Cancellation Selection Components (R_D and C_D) for Required Gain, 1 kΩ Load

| A _v (dB) | R _G (Ω) | C _D (pF) | $R_D(k\Omega)$ |
|---------------------|--------------------|---------------------|----------------|
| 6 | 3 k | Open | 4.3 |
| 9 | 470 | Open | 4.3 |
| 12 | 210 | 0.2 | 4.3 |
| 15 | 120 | 0.3 | 4.3 |
| 18 | 68 | 0.5 | 4.3 |

NARROW-BAND, THIRD-ORDER INTERMODULATION CANCELLATION

Broadband single tone, third-order harmonic optimization does not necessarily result in optimum (minimum) two tone, third-order intermodulation levels. The specified values for C_D and R_D in Table 5 and Table 6 were determined for minimizing broadband, single tone third-order levels.

Due to phase-related distortion coefficients, optimizing single tone third-order distortion does not result in optimum in-band $(2f_1-f_2$ and $2f_2-f_1)$, third-order distortion levels. By proper selection of C_D (using a fixed 4.3 $k\Omega$ R_D), IP3s of better than 45 dBm are achieved. This results in degraded out-of-band, third-order frequencies ($f_2+2f_1,f_1+2f_2,3f_1$ and $3f_2$). Thus, careful frequency planning is required to determine the trade-offs.

Figure 32 shows narrow-band (2 MHz spacing) OIP3 levels optimized at 32 MHz, 70 MHz, 100 MHz, and 180 MHz using the C_D values specified in Figure 33. These four data points (the C_D value and associated OIP3 levels) are extrapolated to provide close estimates of OIP3 levels for any specific frequency between 30 MHz and 180 MHz. For frequencies below ~140 MHz, narrowband tuning of OIP3 results in relatively higher OIP3s (vs. the broadband results shown in Table 2 of the specifications). Though not shown, frequencies below 30 MHz also result in improved OIP3s when using proper values for C_D .

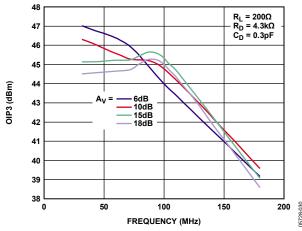


Figure 32. Third-Order Intermodulation Distortion, OIP3 vs. Frequency for Various Gain Settings

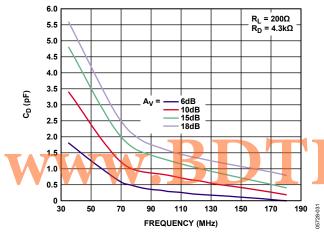


Figure 33. Narrow-Band C_D vs. Frequency for Various Gain Settings

HIGH PERFORMANCE ADC DRIVING

The AD8352 provides the gain, isolation, and balanced low distortion output levels for efficiently driving wideband ADCs such as the AD9445.

Figure 34 and Figure 35 (single and differential input drive) illustrate the typical front-end circuit interface for the AD8352 differentially driving the AD9445 14-bit ADC at 105 MSPS. The AD8352, when used in the single-ended configuration, shows little or no degradation in overall third-order harmonic performance (vs. differential drive). See the Single-Ended Input Operation section. The 100 MHz FFT plots shown in Figure 36 and Figure 37 display the results for the differential configuration. Though not shown, the single-ended, third-order levels are similar.

The 50 Ω resistor shown in Figure 34 provides a 50 Ω differential input impedance to the source for matching considerations. When the driver is less than one eighth of the wavelength from the AD8352, impedance matching is not required thereby negating the need for this termination resistor. The output 24 Ω resistors provide isolation from the analog-to-digital input.

Refer to the Layout and Transmission Line Effects section for more information. The circuit in Figure 35 represents a single-ended input to differential output configuration for driving the AD9445. In this case, the input 50 Ω resistor with $R_{\rm N}$ (typically 200 Ω) provide the input impedance match for a 50 Ω system. Again, if input reflections are minimal, this impedance match is not required. A fixed 200 Ω resistor ($R_{\rm N}$) is required to balance the output voltages that are required for second-order distortion cancellation. $R_{\rm G}$ is the gain setting resistor for the AD8352 with the $R_{\rm D}$ and $C_{\rm D}$ components providing distortion cancellation. The AD9445 presents approximately 2 k Ω in parallel with 5 pF/differential load to the AD8352 and requires a 2.0 V p-p differential signal ($V_{\rm REF}$ = 1 V) between VIN+ and VIN– for a full-scale output operation.

These AD8352 simplified circuits provide the gain, isolation, and distortion performance necessary for efficiently driving high linearity converters, such as the AD9445. This device also provides balanced outputs whether driven differentially or singleended, thereby maintaining excellent second-order distortion levels. However, at frequencies above ~100 MHz, due to phaserelated errors, single-ended, second-order distortion is relatively higher. The output of the amplifier is ac-coupled to allow for an optimum common-mode setting at the ADC input. Input ac coupling can be required if the source also requires a commonmode voltage that is outside the optimum range of the AD8352. A VCM common-mode pin is provided on the AD8352 that equally shifts both input and output common-mode levels. Increasing the gain of the AD8352 increases the system noise and, thus, decreases the SNR (3.5 dB at 100 MHz input for Av = 10 dB)of the AD9445 when no filtering is used. Note that amplifier gains from 3 dB to 18 dB, with proper selection of CD and RD, do not appreciably affect distortion levels. These circuits, when configured properly, can result in SFDR performance of better than 87 dBc at 70 MHz and 82 dBc at 180 MHz input. Single-ended drive, with appropriate C_D and R_D, give similar results for SFDR and thirdorder intermodulation levels shown in these figures.

Placing antialiasing filters between the ADC and the amplifier is a common approach for improving overall noise and broadband distortion performance for both band-pass and low-pass applications. For high frequency filtering, matching to the filter is required. The AD8352 maintains a 100 Ω output impedance well beyond most applications and is well-suited to drive most filter configurations with little or no degradation in distortion.

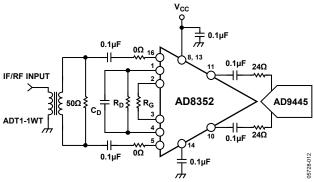


Figure 34. Differential Input to the AD8352 Driving the AD9445

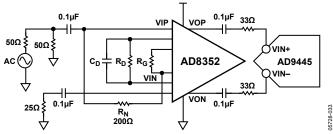


Figure 35. Single-Ended Input to the AD8352 Driving the AD9445

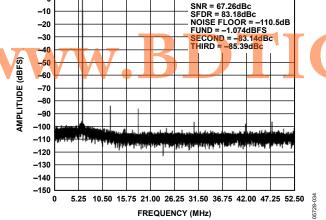


Figure 36. Single Tone Distortion AD8352 Driving AD9445, Encode Clock @ 105 MHz with f_c @ 100 MHz ($A_V = 10$ dB), See Figure 34

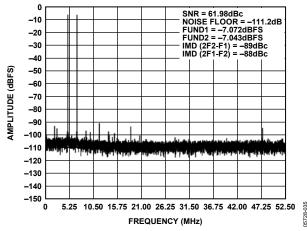


Figure 37. Two Tone Distortion AD8352 Driving AD9445, Encode Clock @ 105 MHz with f_c @ 100 MHz ($A_V = 10$ dB), Analog In = 98 MHz and 101 MHz, See Figure 34

LAYOUT AND TRANSMISSION LINE EFFECTS

High Q inductive drives and loads, as well as stray transmission line capacitance in combination with package parasitics, can potentially form a resonant circuit at high frequencies resulting in excessive gain peaking or possible oscillation. If RF transmission lines connecting the input or output are used, they should be designed such that stray capacitance at the input/output pins is minimized. In many board designs, the signal trace widths should be minimal where the driver/receiver is more than one-eighth of the wavelength from the AD8352. This nontransmission line configuration requires that underlying and adjacent ground and low impedance planes be dropped from the signal lines. In a similar fashion, stray capacitance should be minimized near the R_G, C_D, and R_D components and associated traces. This also requires not placing low impedance planes near these components. Refer to the evaluation board layout (Figure 39 and Figure 40) for more information. Excessive stray capacitance at these nodes results in unwanted high frequency distortion. The 0.1 µF supply decoupling capacitors need to be close to the amplifier. This includes Signal Capacitor C2 through Signal Capacitor C5.

Parasitic suppressing resistors (R5, R6, R7, and R11) can be used at the device input/output pins. Use 25 Ω series resistors (Size 0402) to adequately de-Q the input and output system from most parasitics without a significant decrease in gain. In general, if proper board layout techniques are used, the suppression resistors are not necessarily required. Output Parasitic Suppression Resistor R7 and Output Parasitic Suppression Resistor R11 can be required for driving some switch capacitor ADCs. These suppressors, with Input C of the converter (and possibly added External Shunt C), help provide charge kickback isolation and improve overall distortion at high encode rates.

EVALUATION BOARD

An evaluation board is available for experimentation of various parameters such as gain, common-mode level, and distortion. The output network can be configured for different loads via minor output component changes. The schematic and evaluation board artwork are shown in Figure 38, Figure 39, and Figure 40. All discrete capacitors and resistors are Size 0402, except for C1 (3528-B).

Table 9. Evaluation Board Circuit Components and Functions

| Component | onent Name Function | | Additional Information | |
|---|--|---|---|--|
| C8, C9, C10 | Capacitors | C8, C9, and C10 are bypass capacitors. | C8 = C9 = C10 = 0.1 μF | |
| R_D , C_D | Distortion tuning components | Distortion Adjustment Components. Allows for third-order distortion adjustment HD3. Typically, both are above 300 MHz $C_D = 0.2$ pF, $R_D = 4$ C_D is Panasonic Hi (microwave) mult chip 402 capacito | | |
| R1, R2, R3, R4, R5, R6, T2, C2, C3 | Resistors, transformer, capacitors | Input Interface. R1 and R4 ground one side of the differential drive interface for single-ended applications. T2 is a 1-to-1 impedance ratio balun to transform a single-ended input into a balanced differential signal. R2 and R3 provide a differential 50 Ω input termination. R5 and R6 can be increased to reduce gain peaking when driving from a high source impedance. The 50 Ω T2 = M/A-COM ETC C2 = 0.1 μ F, C3 = 0 termination provides an insertion loss of 6 dB. C2 and C3 provide ac-coupling. | | |
| R7, R8, R9, R11, R12, R13, R14, T1, C4, C5 | Resistors, transformer, capacitors | Output Interface. R13 and R14 ground one side of the differential output interface for single-ended applications. T1 is a 1-to-1 impedance ratio balun to transform a balanced differential signal to a single-ended signal. R8, R9, and R12 are provided for generic placement of matching components. R7 and R11 allow additional output series resistance when driving capacitive loads. The evaluation board is configured to provide a 200 Ω to 50 Ω impedance transformation with an insertion loss of 11.6 dB. C4 and C5 provide ac-coupling. R7 and R11 provide additional series resistance when driving capacitive loads. | R7 = 0 Ω, R8 = 86.6 Ω, R9 = 57.6 Ω, R11 = 0 Ω, R12 = 86.6 Ω, R13 = 0 Ω, R14 = open, T1 = M/A-COM ETC1-1-13, C4 = 0.1 μF, C5 = 0.1 μF | |
| R_{G} | Resistor | Gain Setting Resistor. Resistor R_G is used to set the gain of the device. Refer to Table 5 and Table 6 when selecting the gain resistor. | $R_G = 115 \Omega$ (Size 0402) for a gain of 10 dB | |
| SW1, R18, R19, R20 | Switch, resistors | Enable Interface. R10 connects the enable pin, ENB, to the supply for constant enable operation. The enable function can be toggled by removing R10 and using SW1 to switch between enable and disable modes. | SW1 = installed R18 = R19 = R20 = 0Ω | |
| C1, C6, C7 | Capacitors | Power Supply Decoupling. The supply decoupling consists of a 10 μF capacitor (C1) to ground. C6 and C7 are bypass capacitors. | C1 = 10 μF, C6 = 0.1 μF, C7 = 0.1 μF | |
| T3,T4, C11,C12 | Transformer, capacitors | Calibration Circuit. T3 and T4 are dummy baluns which may be used to calibrate the insertion loss across the transformers in the AD8352 signal chain. | T3 = T4 = M/A-COM ETC1-1-13 C11 = C12 = 0.1 μF | |

EVALUATION BOARD LOADING SCHEMES

The AD8352 evaluation board is characterized with two load configurations representing the most common ADC input resistance. The loads chosen are 200 Ω and 1000 Ω using a broadband resistive match. The loading can be changed via R8, R9, and R12 giving the flexibility to characterize the AD8352 evaluation board for the load in any given application. These loads are inherently lossy and thus must be accounted for in overall gain/loss for the entire evaluation board. Measure the gain of the AD8352 with an oscilloscope using the following procedure to determine the actual gain:

- 1. Measure the peak-to-peak voltage at the input node (C2 or C3).
- 2. Measure the peak-to-peak voltage at the output node (C4 or C5).
- 3. Compute gain using the following formula: Gain = 20log(VOUT/VIN)

Table 10. Values Used for 200 Ω and 1000 Ω Loads

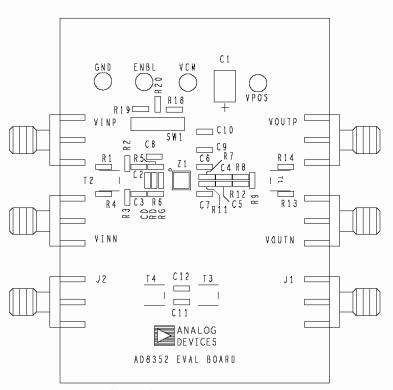
| Component | 200 Ω Load (Ω) | 1000 Ω Load (Ω) |
|-----------|----------------|-----------------|
| R8 | 86.6 | 487 |
| R9 | 57.6 | 51.1 |
| R12 | 86.6 | 487 |

SOLDERING INFORMATION

On the underside of the chip scale package, there is an exposed compressed paddle. This paddle is internally connected to the ground of the chip. Solder the paddle to the low impedance ground plane on the PCB to ensure the specified electrical performance and to provide thermal relief. To further reduce thermal impedance, it is recommended that the ground planes on all layers under the paddle be stitched together with vias.

EVALUATION BOARD SCHEMATICS 710-82720 R9 57.60 O VPOS R8 86.60 0.1 F C7 0.1μF BYPASS CIRCUIT LOCATE CAPS NEAR DUT ŞΣg ₽8\$ — C6 — 0.1µF GND 6.1년 1년 NO N VPOS 오늘 VCM | YELLOW (OPEN PLANES UNDER TRACES) AD8352 28 k OΟΛ OΟΛ ΛCW еир еип ENB RGP RGN SWITCH_SPDT RDP S N **4⊕** ₽ % 55 150 SW1 \$ % B YELLOW CALIBRATION CIRCUIT R_D ≸笼염 C2 1μF 부유를 훈업≹ R3 ₹ 25Ω \$R2 \$25Ω VPOS O-5 **()** → **(** R1 OPEN ₹ 🗇 Þ ₹**⊕**₽

Figure 38. AD8352 Evaluation Board, Version A01212A



WWW.BD Figure 39. Component Side Silkscreen cm/cn/adi

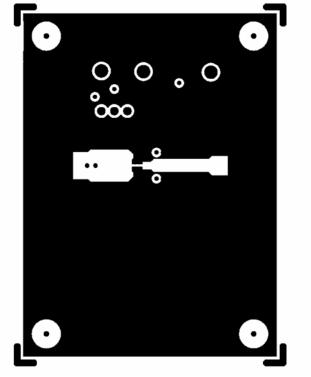


Figure 40. Far Side Showing Ground Plane Pull Back Around Critical Features

OUTLINE DIMENSIONS

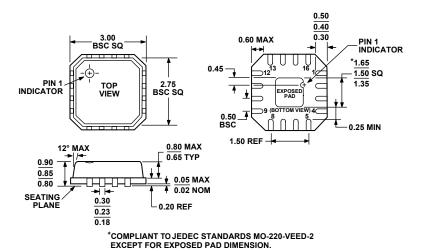


Figure 41. 16-Lead Lead Frame Chip Scale Package [LFCSP_VQ] 3 mm × 3 mm Body, Very Thin Quad (CP-16-3) Dimensions shown in millimeters

ORDERING GUIDE

| | | | Ordering | Package | • |
|----------------------------|-------------------|---|----------|---------|-----------------|
| Model | Temperature Range | Package Description | Quantity | Option | Branding |
| AD8352ACPZ-WP ¹ | -40°C to +85°C | 16-Lead Lead Frame Chip Scale Package [LFCSP_VQ], Waffle Pack | 50 | CP-16-3 | QOR |
| AD8352ACPZ-R7 ¹ | –40°C to +85°C | 16-Lead Lead Frame Chip Scale Package [LFCSP_VQ], 7"Tape and Reel | 3000 | CP-16-3 | Q0R |
| AD8352ACPZ-R2 ¹ | −40°C to +85°C | 16-Lead Lead Frame Chip Scale Package [LFCSP_VQ], 7"Tape and Reel | 250 | CP-16-3 | Q0R |
| AD8352-EVALZ ¹ | | Evaluation Board | | | |

 $^{^{1}}$ Z = RoHS Compliant Part.

| AD8352 |
|--------|
|--------|

NOTES

www.BDTIC.com/cn/adi